



## Product brief

# 1EDN7550 and 1EDN8550 EiceDRIVER™

1-channel low-side gate driver family with truly differential inputs prevents false triggering of power MOSFETs

### Overview:

- > The input signal levels of conventional low-side gate driver ICs are referenced to the ground potential of the gate driver IC. If in the application the ground potential of the gate driver IC shifts excessively false triggering of the gate driver IC can occur.
- > The 1EDN7550/1EDN8550 gate driver ICs have truly differential inputs. Their control signal inputs are largely independent from the ground potential. Only the voltage difference between its input contacts is relevant.  
**This prevents false triggering of power MOSFETs.**

### Applications

- > Server
- > Telecom
- > DC-DC converters
- > Telecom bricks
- > Power tools
- > Industrial SMPS
- > Wireless charging
- > Solar micro inverter

### Product features

- > Truly differential inputs
- > 4 A source current
- > 8 A sink current
- > Separate source/sink outputs
- > Low-ohmic output stage
- > 29 ns input minimum pulse width
- > 7 ns propagation delay accuracy
- > 5 A reverse current robustness of the outputs
- > 4 V and 8 V UVLO versions
- > SOT-23 package, 6-pins

### Product benefits

- > Control inputs independent from gate driver GND
- > Fast Miller plateau transition
- > Fast shut-off
- > No diode voltage drop → Near zero gate voltage at turn-off
- > Low power dissipation within gate driver IC
- > Up to 15 MHz switching speed
- > Precise
- > No schottky clamping diodes required
- > Fast and reliable MOSFET turn-off
- > Small

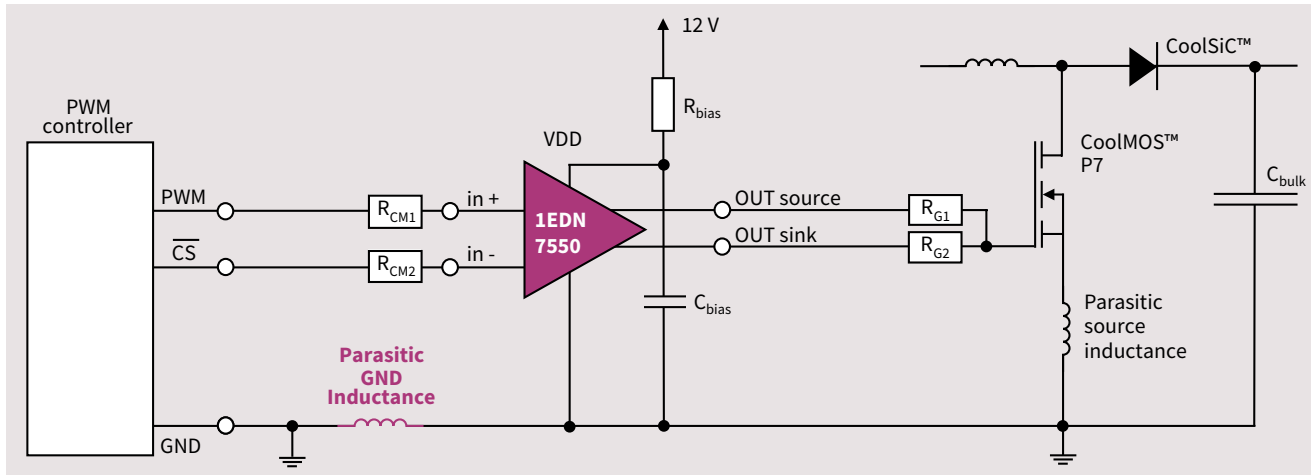
### Application benefits

- > Robust against ground shifts from power MOSFET switching
- > Low MOSFET switching losses
- > Robust against false MOSFET triggering
- > Highest effective MOSFET driving power
- > Efficiency gains
- > Increased power density and BOM savings
- > Instant MOSFET protection under abnormal operation
- > High power density

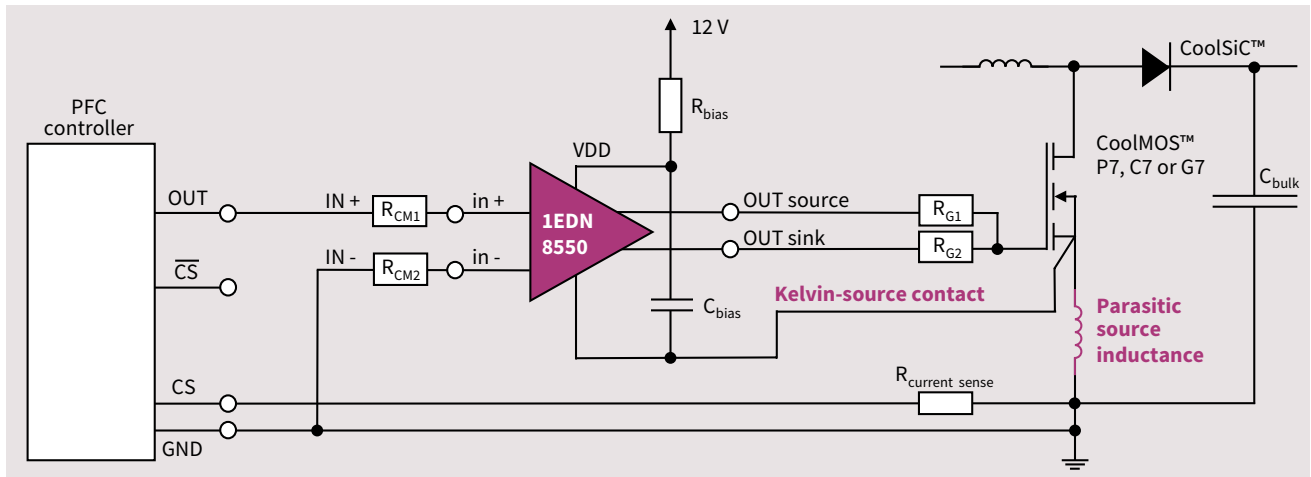


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## 1EDN7550 driving CoolMOS™ SJ MOSFET on 1-layer PCB



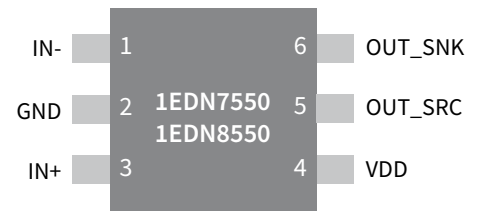
## 1EDN8550 driving Kelvin source CoolMOS™ SJ MOSFET in boost PFC



## Product portfolio

Type	Ground shift robustness		UVLO	Package
	dynamic	static		
1EDN7550B	+/- 150 V	+/- 70 V	4 V	6-pin SOT-23
1EDN8550B	+/- 150 V	+/- 70 V	8 V	6-pin SOT-23

## Pinout



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